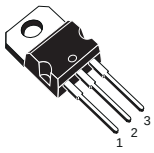
STGP12NB60KD - STGB12NB60KD

N-CHANNEL 18A - 600V TO-220/D²PAK
SHORT CIRCUIT PROOF PowerMESH™ IGBT

TYPE	V_{CES}	$V_{CE(sat)}$ (Max) @25°C	I_C(#) @ 100°C
STGP12NB60KD	600 V	< 2.8 V	18 A
STGB12NB60KD	600 V	< 2.8 V	18 A

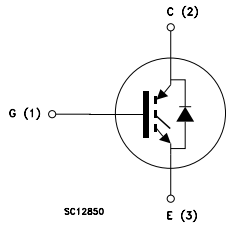
- HIGH INPUT IMPEDANCE
- LOW ON-LOSSES
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- OFF LOSSES INCLUDE TAIL CURRENT
- VERY HIGH FREQUENCY OPERATION
- TYPICAL SHORT CIRCUIT WITHSTAND TIME 10 MICROS
- CO-PACKAGED ANTIPARALLEL DIODE



TO-220

D²PAK

INTERNAL SCHEMATIC DIAGRAM



DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix "K" identifies a family optimized for high frequency applications (up to 50kHz) and short circuit proof in order to achieve very high switching performances (reduced tfall) mantaining a low voltage drop.

APPLICATIONS

- HIGH FREQUENCY MOTOR CONTROLS
- SMPS
- UPS

ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STGP12NB60KD	GP12NB60KD	TO-220	TUBE
STGB12NB60KDT4	GB12NB60KD	D²PAK	TAPE & REEL

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage (V_{GS} = 0)	600	V
V_{ECR}	Emitter-Collector Voltage	20	V
V_{GE}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current (continuous) at T_C = 25°C (#)	30	A
I_C	Collector Current (continuous) at T_C = 100°C (#)	18	A
I_{CM} (•)	Collector Current (pulsed)	60	A
Tsc	Short Circuit Withstand	10	µs
P_{TOT}	Total Dissipation at T_C = 25°C	125	W
	Derating Factor	1.0	W/°C
T_{stg}	Storage Temperature	–65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	1.0	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{BR(CES)}$	Collector-Emitter Breakdown Voltage	I_C = 250 µA, V_{GE} = 0	600			V
I_{CES}	Collector cut-off (V_{GE} = 0)	V_{CE} = Max Rating, T_C = 25 °C V_{CE} = Max Rating, T_C = 125 °C			50 100	µA µA
I_{GES}	Gate-Emitter Leakage Current (V_{CE} = 0)	V_{GE} = ± 20V , V_{CE} = 0			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Threshold Voltage	V_{CE} = V_{GE}, I_C = 250 µA	5		7	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	V_{GE} = 15V, I_C = 12 A V_{GE} = 15V, I_C = 12 A, Tj =125°C		2.2 1.7	2.8	V V

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs}	Forward Transconductance	V_{CE} = 25 V , I_C = 12 A		5		S
C_{ies} C_{oes} C_{res}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{CE} = 25V, f = 1 MHz, V_{GE} = 0		890 110 22		pF pF pF
Q_g Q_{ge} Q_{gc}	Total Gate Charge Gate-Emitter Charge Gate-Collector Charge	V_{CE} = 480V, I_C = 12 A, V_{GE} = 15V		54 8 31		nC nC nC
I_{CL}	Latching Current	V_{clamp} = 480 V , V_{GE} =15V, Tj = 125°C , R_G = 10 Ω		48		A
T_{wsc}	Short Circuit WITHSTAND Time	V_{CE} = 0.5 BV_{ces} , V_{GE} = 15 V Tj = 125°C , R_G = 10 Ω	10			µs

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	V_{CC} = 480 V, I_C = 12 A		25		ns
t_r	Rise Time	R_G = 10Ω , V_{GE} = 15 V		14.5		ns
$(di/dt)_{on}$	Turn-on Current Slope	V_{CC}= 480 V, I_C = 12 A R_G=10Ω		590		A/µs
Eon	Turn-on Switching Losses	V_{GE} = 15 V,Tj = 125°C		180		µJ

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t_c	Cross-over Time	V_{cc} = 480 V, I_C = 12 A,		130		ns
$t_r(V_{off})$	Off Voltage Rise Time	R_{GE} = 10 Ω , V_{GE} = 15 V		25		ns
$t_{d(off)}$	Delay Time			96		ns
t_f	Fall Time			100		ns
E_{off}(**)	Turn-off Switching Loss			258		µJ
E_{ts}	Total Switching Loss			410		µJ
t_c	Cross-over Time	V_{cc} = 480 V, I_C = 12 A,		310		ns
$t_r(V_{off})$	Off Voltage Rise Time	R_{GE} = 10 Ω , V_{GE} = 15 V		80		ns
$t_{d(off)}$	Delay Time	Tj = 125 °C		150		ns
t_f	Fall Time			220		ns
E_{off}(**)	Turn-off Switching Loss			650		µJ
E_{ts}	Total Switching Loss			830		µJ

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by max. junction temperature.
(**)Losses include Also the Tail (Jedec Standardization)

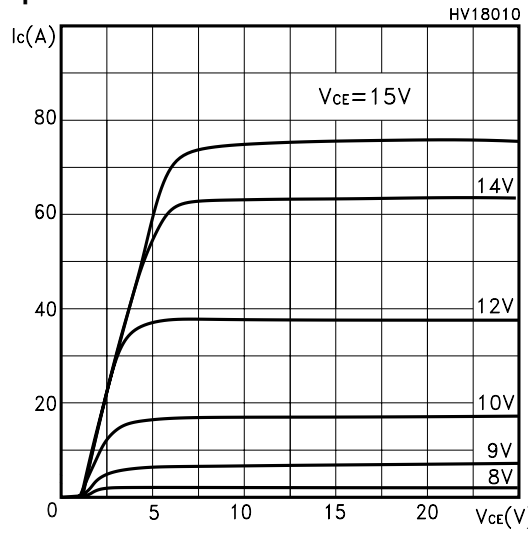
COLLECTOR-EMITTER DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_f	Forward Current				12	A
I_{fm}	Forward Current pulsed				48	A
V_f	Forward On-Voltage	I_f = 6 A		1.3	1.9	V
		I_f = 6 A, Tj = 125 °C		1.1		V
t_{rr}	Reverse Recovery Time	I_f = 6 A ,V_R = 50 V,		80		ns
Q_{rr}	Reverse Recovery Charge	Tj =125°C, di/dt = 100 A/µs		240		nC
I_{rrm}	Reverse Recovery Current			5.5		A

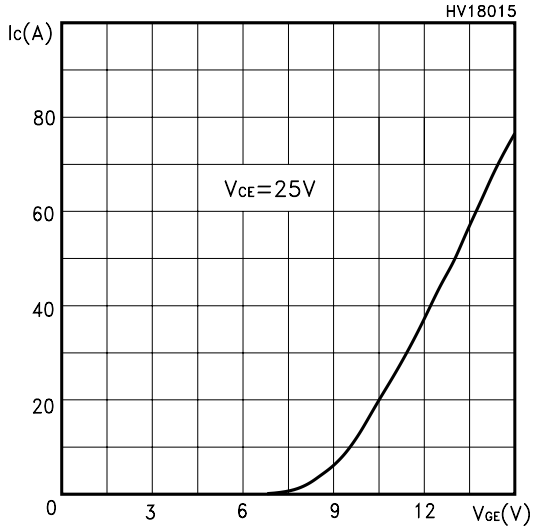
(#) Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C, I_C)}$$

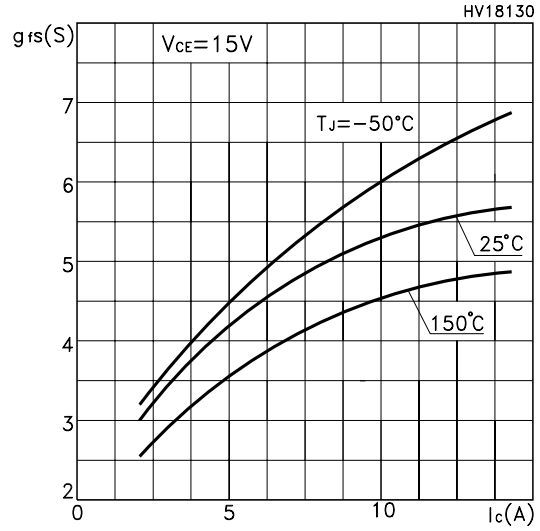
Output Characteristics



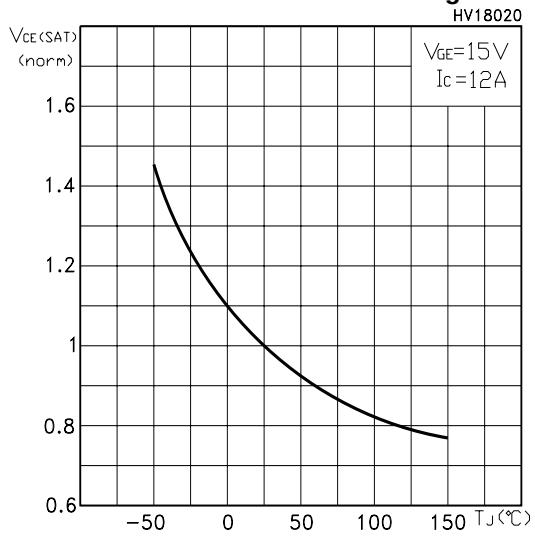
Transfer Characteristics



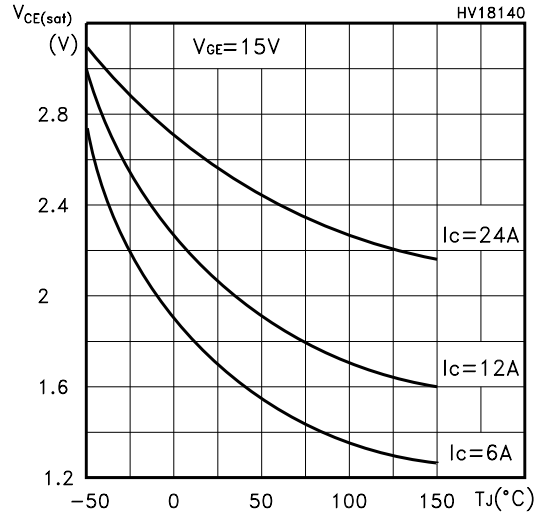
Transconductance



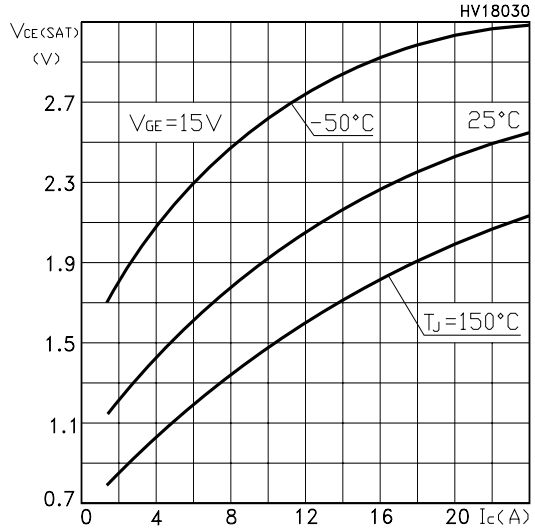
Normalized Collector-Emitter On Voltage vs Temp.



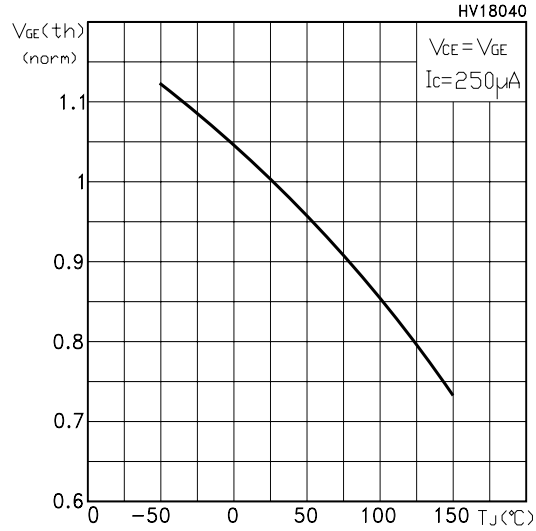
Collector-Emitter On Voltage vs Temperature



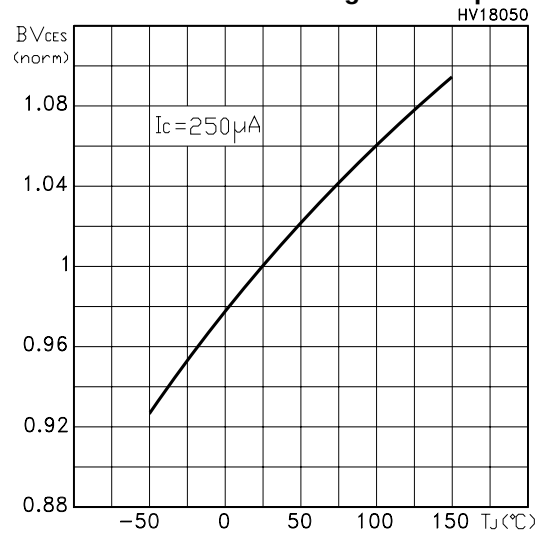
Collector-Emitter On Voltage vs Collector Current



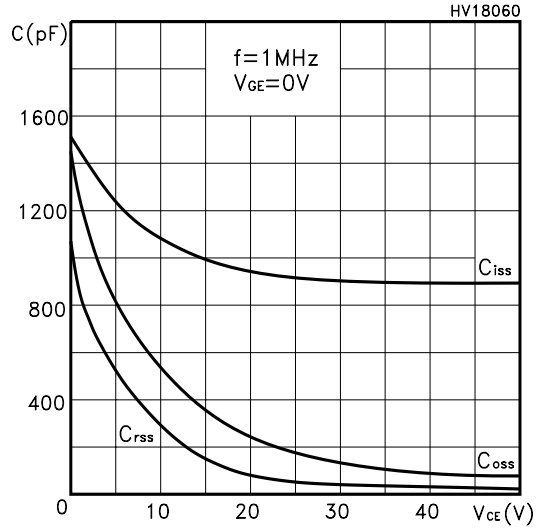
Gate Threshold vs Temperature



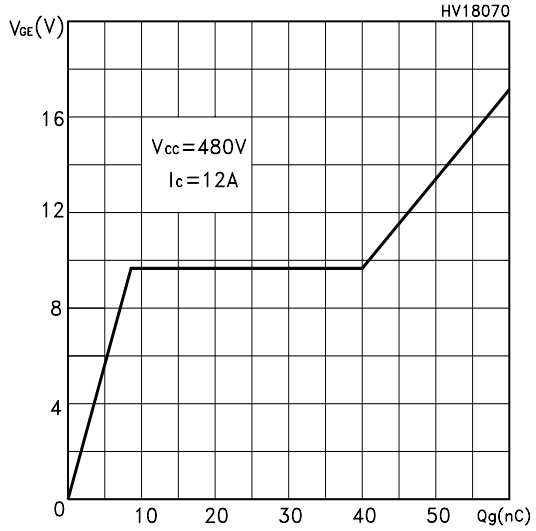
Normalized Breakdown Voltage vs Temperature



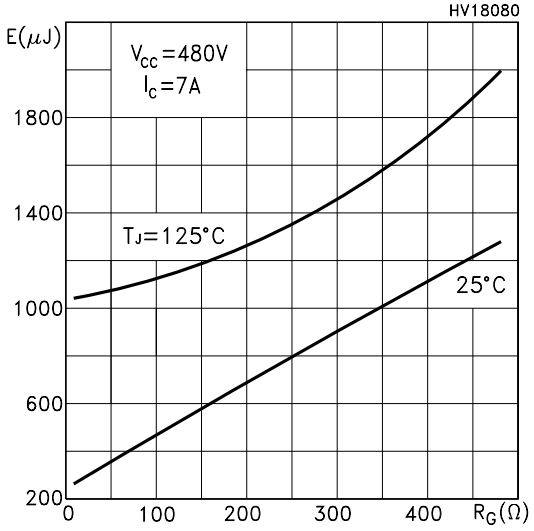
Capacitance Variations



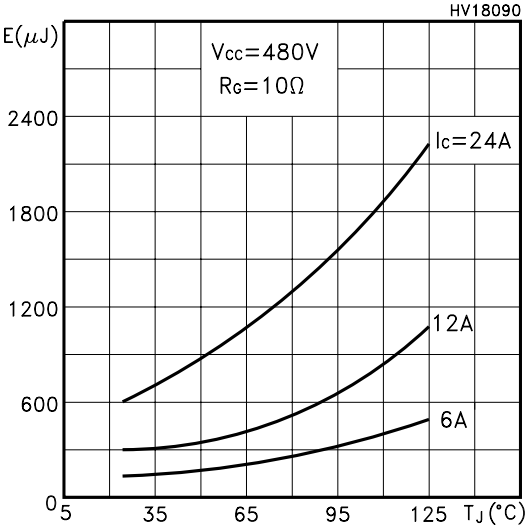
Gate Charge vs Gate-Emitter Voltage



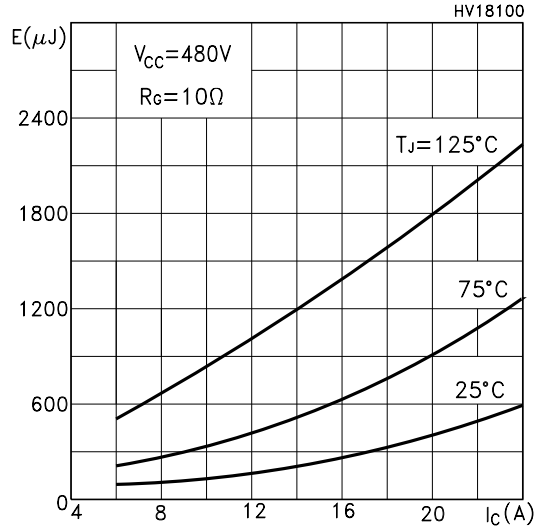
Total Switching Losses vs Gate Resistance



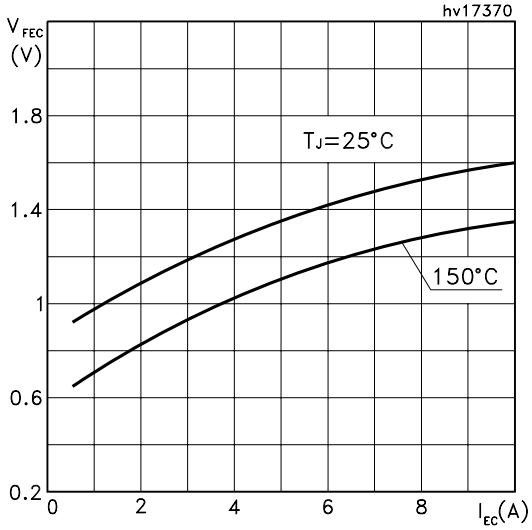
Total Switching Losses vs Temperature



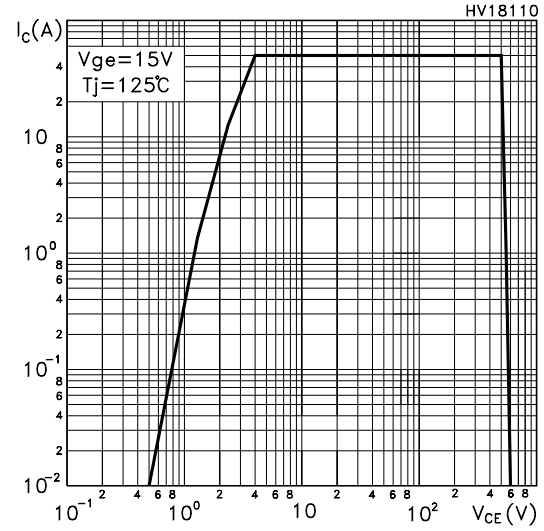
Total Switching Losses vs Collector Current



Diode Forward Voltage



Turn-Off SOA



Thermal Impedance

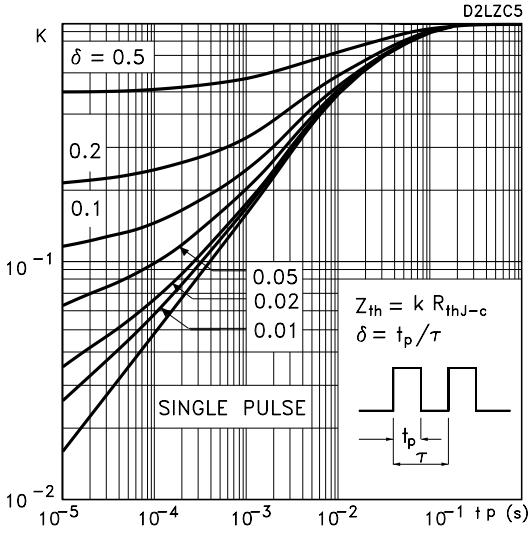


Fig. 1: Gate Charge test Circuit

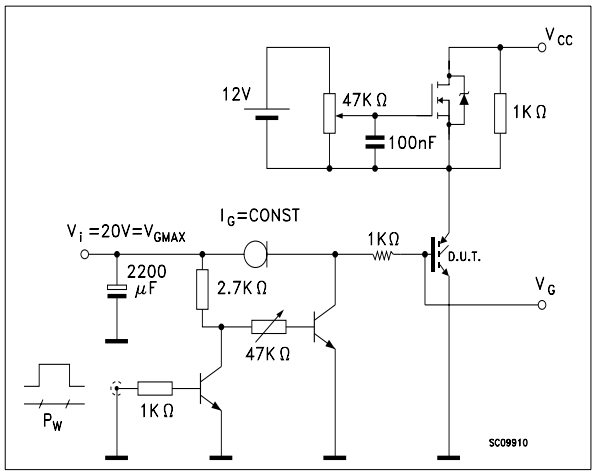
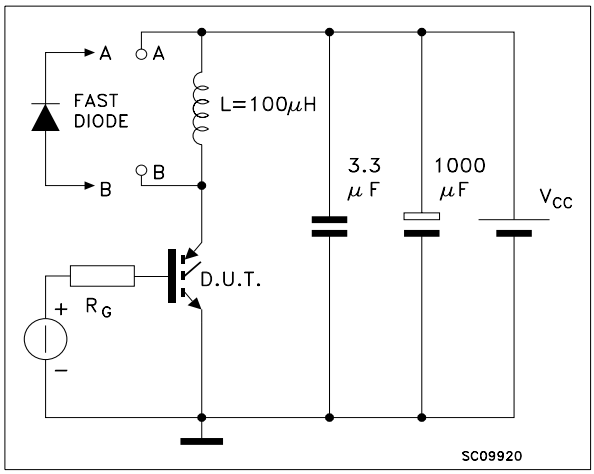
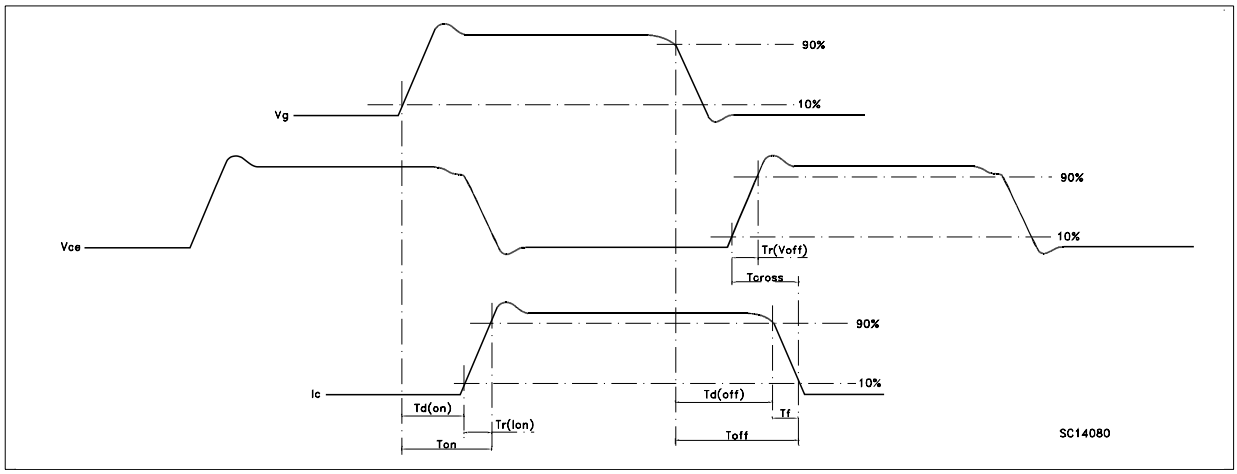


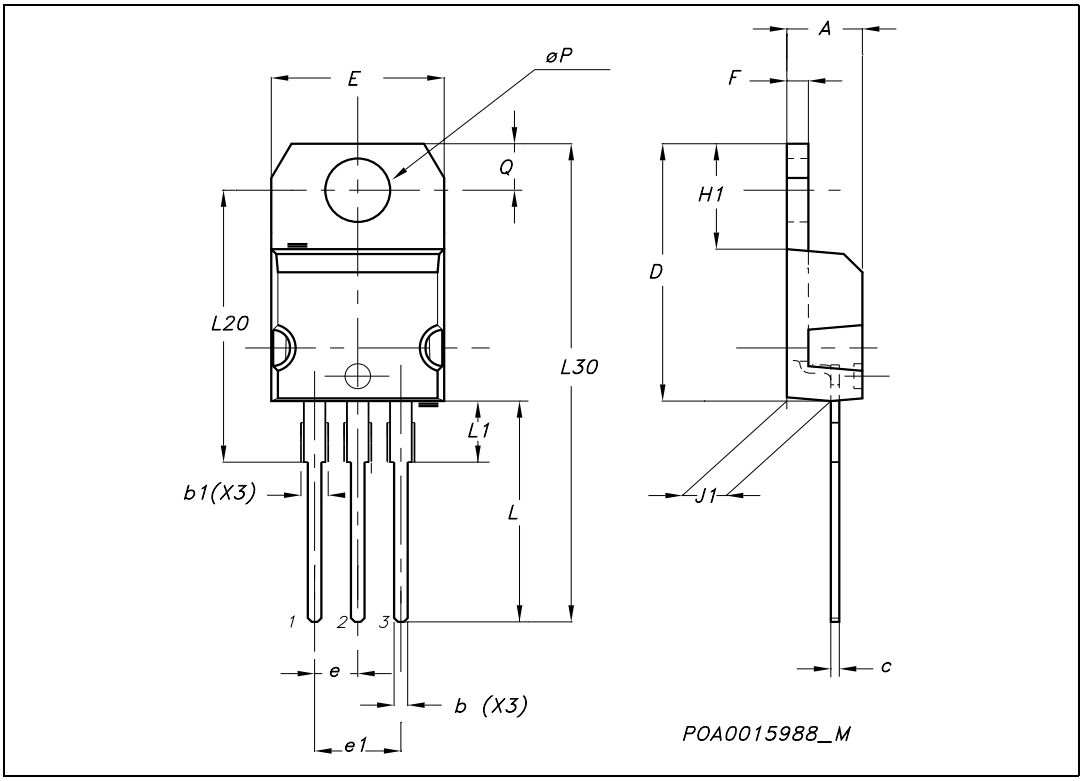
Fig. 2: Test Circuit For Inductive Load Switching





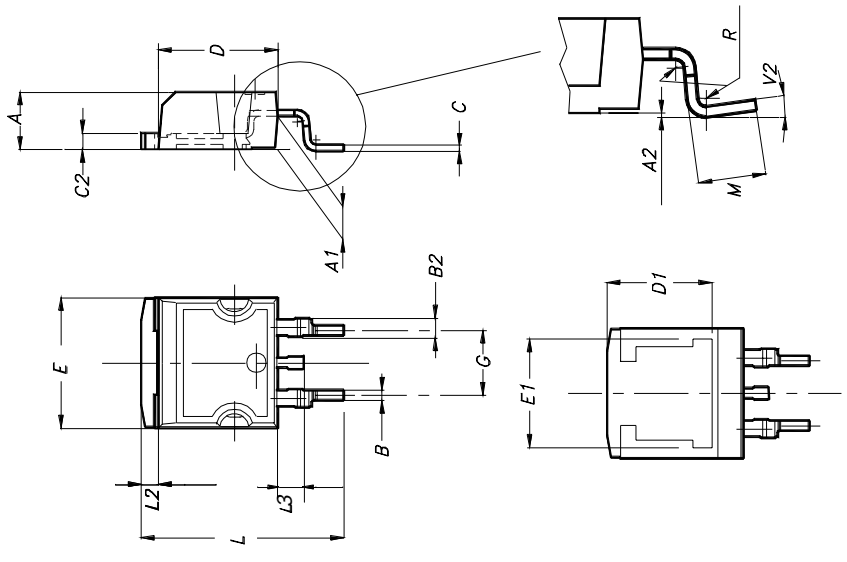
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116

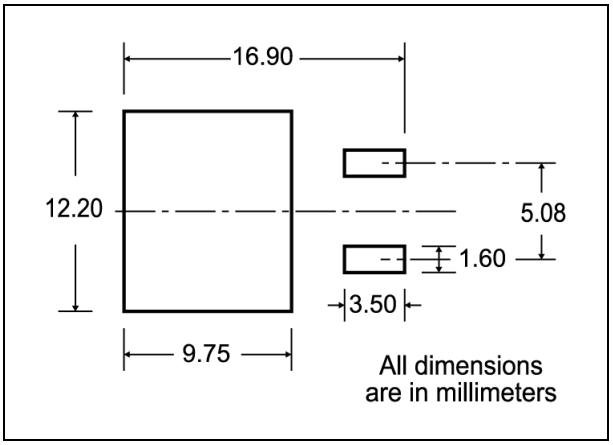


D^2PAK MECHANICAL DATA

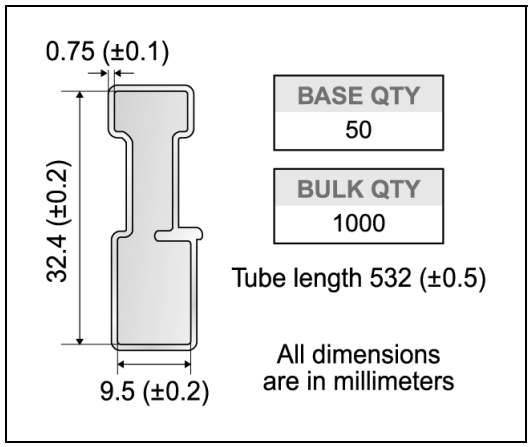
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0º		8º			



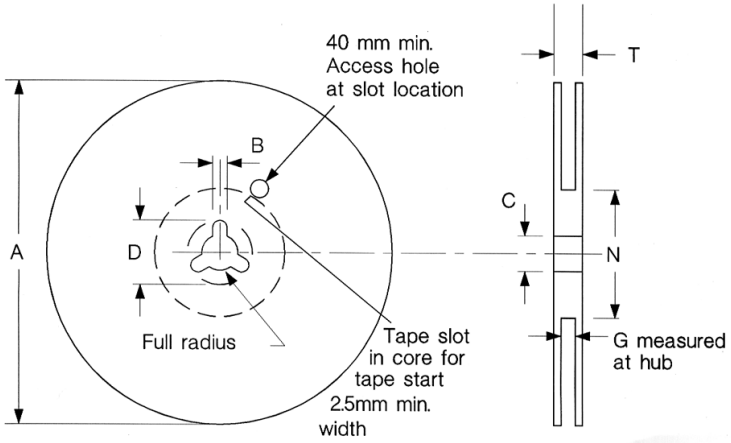
D^2PAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*



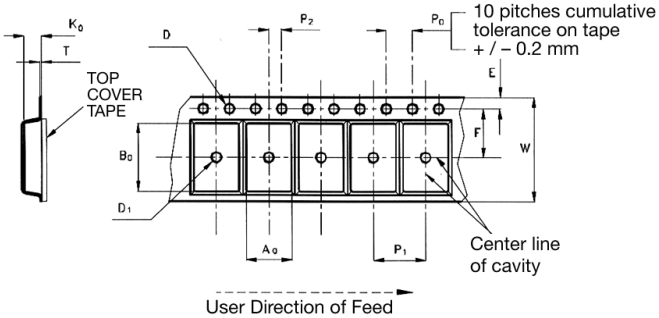
REEL MECHANICAL DATA

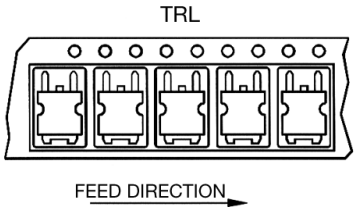
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

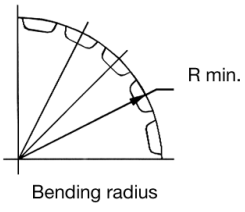
BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956







* on sales type